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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status Core Processor	Obsolete PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8349evvajd

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

- Double data rate, DDR1/DDR2 SDRAM memory controller
 - Programmable timing supporting DDR1 and DDR2 SDRAM
 - 32- or 64-bit data interface, up to 400 MHz data rate
 - Up to four physical banks (chip selects), each bank up to 1 Gbyte independently addressable
 - DRAM chip configurations from 64 Mbits to 1 Gbit with $\times 8/\times 16$ data ports
 - Full error checking and correction (ECC) support
 - Support for up to 16 simultaneous open pages (up to 32 pages for DDR2)
 - Contiguous or discontiguous memory mapping
 - Read-modify-write support
 - Sleep-mode support for SDRAM self refresh
 - Auto refresh
 - On-the-fly power management using CKE
 - Registered DIMM support
 - 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- Dual three-speed (10/100/1000) Ethernet controllers (TSECs)
 - Dual controllers designed to comply with IEEE 802.3TM, 802.3uTM, 820.3xTM, 802.3zTM, 802.3acTM standards
 - Ethernet physical interfaces:
 - 1000 Mbps IEEE Std. 802.3 GMII/RGMII, IEEE Std. 802.3z TBI/RTBI, full-duplex
 - 10/100 Mbps IEEE Std. 802.3 MII full- and half-duplex
 - Buffer descriptors are backward-compatible with MPC8260 and MPC860T 10/100 programming models
 - 9.6-Kbyte jumbo frame support
 - RMON statistics support
 - Internal 2-Kbyte transmit and 2-Kbyte receive FIFOs per TSEC module
 - MII management interface for control and status
 - Programmable CRC generation and checking
- Dual PCI interfaces
 - Designed to comply with PCI Specification Revision 2.3
 - Data bus width options:
 - Dual 32-bit data PCI interfaces operating at up to 66 MHz
 - Single 64-bit data PCI interface operating at up to 66 MHz
 - PCI 3.3-V compatible
 - PCI host bridge capabilities on both interfaces
 - PCI agent mode on PCI1 interface
 - PCI-to-memory and memory-to-PCI streaming
 - Memory prefetching of PCI read accesses and support for delayed read transactions
 - Posting of processor-to-PCI and PCI-to-memory writes

Electrical Characteristics

- Dual industry-standard I²C interfaces
 - Two-wire interface
 - Multiple master support
 - Master or slave I²C mode support
 - On-chip digital filtering rejects spikes on the bus
 - System initialization data optionally loaded from I²C-1 EPROM by boot sequencer embedded hardware
- DMA controller
 - Four independent virtual channels
 - Concurrent execution across multiple channels with programmable bandwidth control
 - Handshaking (external control) signals for all channels: DMA_DREQ[0:3],
 DMA_DACK[0:3], DMA_DDONE[0:3]
 - All channels accessible to local core and remote PCI masters
 - Misaligned transfer capability
 - Data chaining and direct mode
 - Interrupt on completed segment and chain
- DUART
 - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Serial peripheral interface (SPI) for master or slave
- General-purpose parallel I/O (GPIO)
 - 64 parallel I/O pins multiplexed on various chip interfaces
- System timers
 - Periodic interrupt timer
 - Real-time clock
 - Software watchdog timer
 - Eight general-purpose timers
- Designed to comply with IEEE Std. 1149.1TM, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8349EA. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 **Overall DC Electrical Characteristics**

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings	s ¹
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	Parameter	Symbol	Max Value	Unit	Notes
Core supply voltage		V _{DD}	–0.3 to 1.32 (1.36 max for 667-MHz core frequency)	V	_
PLL supply voltage		AV _{DD}	-0.3 to 1.32 (1.36 max for 667-MHz core frequency)	V	—
DDR and DDR2 DR	AM I/O voltage	GV _{DD}	-0.3 to 2.75 -0.3 to 1.98	V	—
Three-speed Ethernet I/O, MII management voltage		LV _{DD}	-0.3 to 3.63	V	—
PCI, local bus, DUA and JTAG I/O voltag	RT, system control and power management, I ² C, le	OV _{DD}	-0.3 to 3.63	V	—
Input voltage	DDR DRAM signals	MV _{IN}	–0.3 to (GV _{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV _{REF}	–0.3 to (GV _{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV _{IN}	-0.3 to (LV _{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I ² C, and JTAG signals	OV _{IN}	-0.3 to (OV _{DD} + 0.3)	V	3, 5
	PCI	OV _{IN}	-0.3 to (OV _{DD} + 0.3)	V	6
Storage temperature	e range	T _{STG}	-55 to 150	°C	—

Notes:

¹ Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.

- ² Caution: MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ³ **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ⁴ **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- ⁵ (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
- 6 OVIN on the PCI interface can overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

Figure 3 shows the undershoot and overshoot voltage of the PCI interface of the MPC8349EA for the 3.3-V signals, respectively.

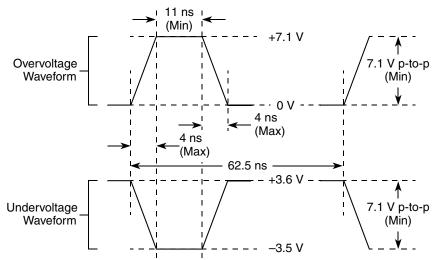


Figure 3. Maximum AC Waveforms on PCI Interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

Table 3 provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	40	OV _{DD} = 3.3 V
PCI signals (not including PCI output clocks)	25	
PCI output clocks (including PCI_SYNC_OUT)	40	
DDR signal	18	GV _{DD} = 2.5 V
DDR2 signal	18 36 (half-strength mode)	GV _{DD} = 1.8 V
TSEC/10/100 signals	40	LV _{DD} = 2.5/3.3 V
DUART, system control, I ² C, JTAG, USB	40	OV _{DD} = 3.3 V
GPIO signals	40	OV _{DD} = 3.3 V, LV _{DD} = 2.5/3.3 V

Table 3. Output Drive Capability

2.2 **Power Sequencing**

This section details the power sequencing considerations for the MPC8349EA.

2.2.1 Power-Up Sequencing

MPC8349EA does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD} , LV_{DD} , and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power

RESET Initialization

Table 9. RESET Pins DC Electrical Characteristics¹ (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Output low voltage	V _{OL}	l _{OL} = 3.2 mA	_	0.4	V

Notes:

1. This table applies for pins PORESET, HRESET, SRESET, and QUIESCE.

2. HRESET and SRESET are open drain pins, thus V_{OH} is not relevant for those pins.

5.2 **RESET AC Electrical Characteristics**

Table 10 provides the reset initialization AC timing specifications of the MPC8349EA.

Table 10. RESET Initialization Timing Specifications

Parameter	Min	Мах	Unit	Notes
Required assertion time of HRESET or SRESET (input) to activate reset flow	32	—	t _{PCI_SYNC_IN}	1
Required assertion time of $\overrightarrow{\text{PORESET}}$ with stable clock applied to CLKIN when the MPC8349EA is in PCI host mode	32	—	t _{CLKIN}	2
Required assertion time of PORESET with stable clock applied to PCI_SYNC_IN when the MPC8349EA is in PCI agent mode	32	_	t _{PCI_SYNC_IN}	1
HRESET/SRESET assertion (output)	512	—	t _{PCI_SYNC_IN}	1
HRESET negation to SRESET negation (output)	16	—	t _{PCI_SYNC_IN}	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8349EA is in PCI host mode	4	—	t _{CLKIN}	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the MPC8349EA is in PCI agent mode	4	_	^t PCI_SYNC_IN	1
Input hold time for POR configuration signals with respect to negation of HRESET	0	—	ns	—
Time for the MPC8349EA to turn off POR configuration signals with respect to the assertion of HRESET	—	4	ns	3
Time for the MPC8349EA to turn on POR configuration signals with respect to the negation of $\overline{\text{HRESET}}$	1	—	t _{PCI_SYNC_IN}	1, 3

Notes:

1. t_{PCI_SYNC_IN} is the clock period of the input clock applied to PCI_SYNC_IN. In PCI host mode, the primary clock is applied to the CLKIN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. See the *MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual*.

2. t_{CLKIN} is the clock period of the input clock applied to CLKIN. It is valid only in PCI host mode. See the MPC8349EA PowerQUICC II Pro Integrated Host Processor Family Reference Manual.

3. POR configuration signals consist of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

DDR and DDR2 SDRAM

Table 19 provides the input AC timing specifications for the DDR SDRAM interface.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC/MDM	t _{CISKEW}			ps	1, 2
400 MHz		-600	600		3
333 MHz		-750	750		—
266 MHz		-750	750		—
200 MHz		-750	750		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.

- The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the equation: t_{DISKEW} = ± (T/4 – abs (t_{CISKEW})); where T is the clock period and abs (t_{CISKEW}) is the absolute value of t_{CISKEW}.
- 3. This specification applies only to the DDR interface.

Figure 5 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

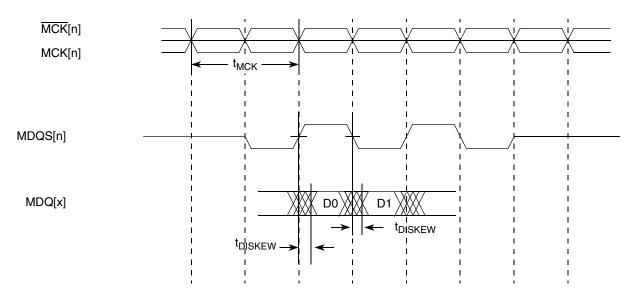


Figure 5. DDR Input Timing Diagram

Table 26. GMII Receive AC Timing Specifications (continued)

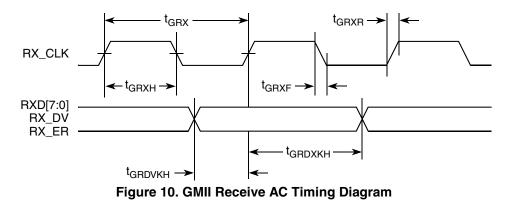
At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
RX_CLK clock rise (20%–80%)	t _{GRXR}	_	_	1.0	ns
RX_CLK clock fall time (80%–20%)	t _{GRXF}	_	_	1.0	ns

Note:

1. The symbols for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

Figure 10 shows the GMII receive AC timing diagram.



8.2.2 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.2.1 MII Transmit AC Timing Specifications

Table 27 provides the MII transmit AC timing specifications.

Table 27. Mll Transm	it AC Timing	Specifications
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At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.
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Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
TX_CLK clock period 10 Mbps	t _{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t _{MTX}	—	40	_	ns
TX_CLK duty cycle	t _{MTXH} /t _{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t _{MTKHDX}	1	5	15	ns

Table 28. MII Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RX_CLK clock rise (20%–80%)	t _{MRXR}	1.0	_	4.0	ns
RX_CLK clock fall time (80%–20%)	t _{MRXF}	1.0	_	4.0	ns

Note:

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub>

Figure 12 provides the AC test load for TSEC.

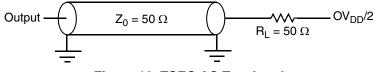


Figure 12. TSEC AC Test Load

Figure 13 shows the MII receive AC timing diagram.

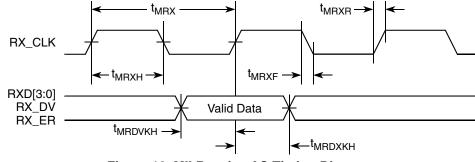


Figure 13. MII Receive AC Timing Diagram

8.2.3 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

Local Bus

Figure 21 through Figure 26 show the local bus signals.

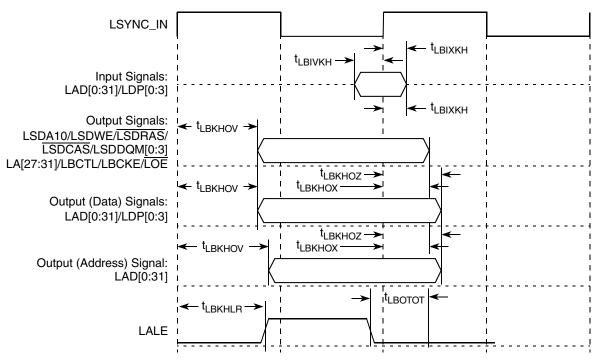


Figure 21. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

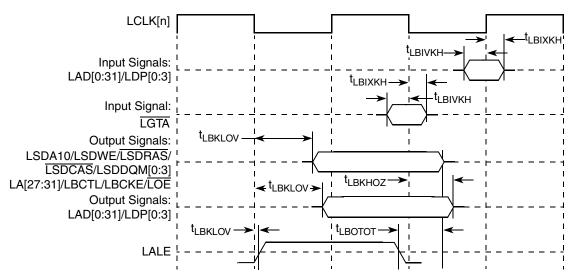


Figure 22. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)



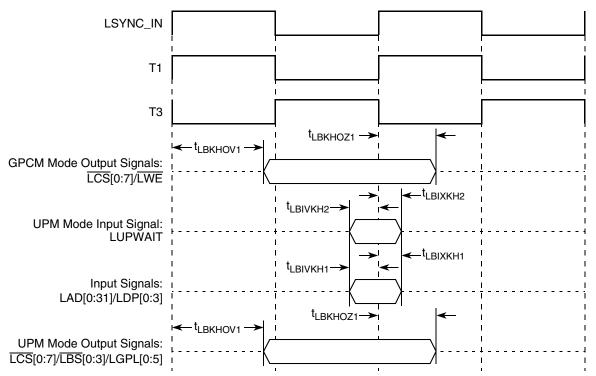


Figure 23. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

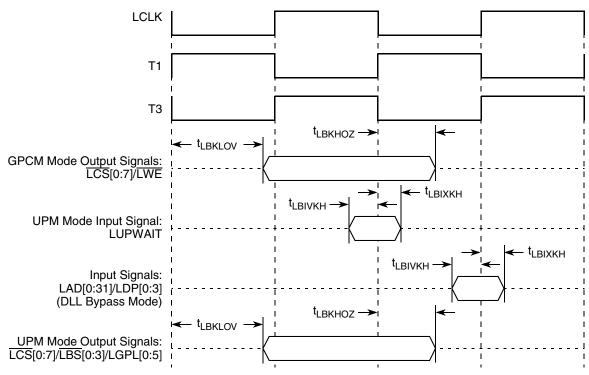


Figure 24. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

Table 41. JTAG AC Timing Specifications (Independent of CLKIN)¹ (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Мах	Unit	Notes
JTAG external clock to output high impedance: Boundary-scan data TDO	t _{jtkldz} t _{jtkloz}	2 2	19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 18). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.

2. The symbols for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

3. TRST is an asynchronous level sensitive signal. The setup time is for test purposes only.

4. Non-JTAG signal input timing with respect to t_{TCLK}.

5. Non-JTAG signal output timing with respect to t_{TCLK}.

6. Guaranteed by design and characterization.

Figure 27 provides the AC test load for TDO and the boundary-scan outputs of the MPC8349EA.

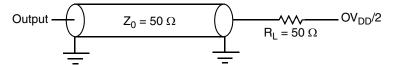


Figure 27. AC Test Load for the JTAG Interface

Figure 28 provides the JTAG clock input timing diagram.

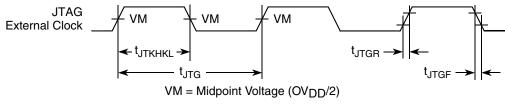
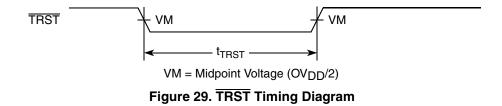


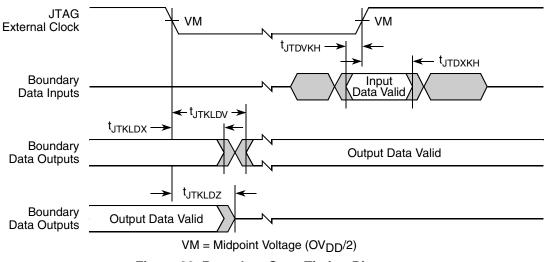
Figure 28. JTAG Clock Input Timing Diagram

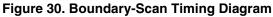
Figure 29 provides the $\overline{\text{TRST}}$ timing diagram.

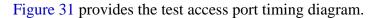


JTAG

Figure 30 provides the boundary-scan timing diagram.







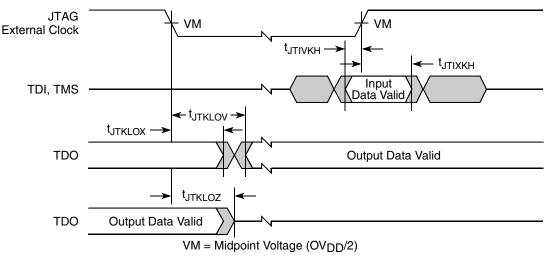




Table 47. Timer DC Electrical Characteris	tics (continued)
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Parameter	Symbol	Condition	Min	Мах	Unit
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

14.2 Timer AC Timing Specifications

Table 48 provides the timer input and output AC timing specifications.

Table 48. Timers Input AC Timing Specifications¹

Parameter	Symbol ²	Min	Unit
Timers inputs—minimum pulse width	t _{TIWID}	20	ns

Notes:

1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.

2. Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

15 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

15.1 GPIO DC Electrical Characteristics

Table 49 provides the DC electrical characteristics for the MPC8349EA GPIO.

Table 49. GPIO DC Electrical Characteristics

PArameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V _{IH}	—	2.0	OV _{DD} + 0.3	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	—	—	±5	μA
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

Package and Pin Listings

Signal	Package Pin Number	Pin Type	Power Supply	Notes
GND	 A1, A34, C1, C7, C10, C11, C15, C23, C25, C28, D1, D8, D20, D30, E7, E13, E15, E17, E18, E21, E23, E25, E32, F6, F19, F27, F30, F34, G31, H5, J4, J34, K30, L5, M2, M5, M30, M33, N3, N5, P30, R5, R32, T5, T30, U6, U29, U33, V2, V5, V30, W6, W30, Y30, AA2, AA30, AB2, AB6, AB30, AC3, AC6, AD31, AE5, AF2, AF5, AF31, AG30, AG31, AH4, AJ3, AJ19, AJ22, AK7, AK13, AK14, AK16, AK18, AK20, AK25, AK28, AL3, AL5, AL10, AL12, AL22, AL27, AM1, AM6, AM7, AN12, AN17, AN34, AP1, AP8, AP34 	_	_	_
GV _{DD}	A2, E2, G5, G6, J5, K4, K5, L4, N4, P5, R6, T6, U5, V1, W5, Y5, AA4, AB3, AC4, AD5, AF3, AG5, AH2, AH5, AH6, AJ6, AK6, AK8, AK9, AL6	Power for DDR DRAM I/O voltage (2.5 V)	GV _{DD}	—
LV _{DD1}	C9, D11	Power for three speed Ethernet #1 and for Ethernet management interface I/O (2.5 V, 3.3 V)	LV _{DD1}	_
LV _{DD2}	C6, D9	Power for three speed Ethernet #2 I/O (2.5 V, 3.3 V)	LV _{DD2}	_
V _{DD}	E19, E29, F7, F9, F11, F13, F15, F17, F18, F21, F23, F25, F29, H29, J6, K29, M29, N6, P29, T29, U30, V6, V29, W29, AB29, AC5, AD29, AF6, AF29, AH29, AJ8, AJ12, AJ14, AJ16, AJ18, AJ20, AJ21, AJ23, AJ25, AJ26, AJ27, AJ28, AJ29, AK10	Power for core (1.2 V nominal, 1.3 V for 667 MHz)	V _{DD}	
OV _{DD}	B22, B28, C16, C17, C24, C26, D13, D15, D19, D29, E31, F28, G33, H30, L29, L32, N32, P31, R31, U32, W31, Y29, AA29, AC30, AE31, AF30, AG29, AJ17, AJ30, AK11, AL15, AL19, AL21, AL29, AL30, AM20, AM23, AM24, AM26, AM28, AN11, AN13	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV _{DD}	_
MVREF1	M3	I	DDR reference voltage	

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

RCWL[SPMF]	System PLL Multiplication Factor
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

Table 58. System	PLL Multiplication	Factors (continued)
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As described in Section 19, "Clocking," the LBIUCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 59 and Table 60 show the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

CFG_CLKIN_DIV at Reset ¹			Input Clock Frequency (MHz) ²					
	SPMF	<i>csb_clk</i> : Input Clock Ratio ²	16.67	25	33.33	66.67		
			csb_clk Frequency			lz)		
Low	0010	2 : 1				133		
Low	0011	3 : 1			100	200		
Low	0100	4 : 1		100	133	266		
Low	0101	5 : 1		125	166	333		

Table 59. CSB Frequency Options for Host Mode

			li	nput Clock Fre	equency (MHz) ²
CFG_CLKIN_DIV at Reset ¹	SPMF	<i>csb_clk</i> : Input Clock Ratio ²	16.67	25	33.33	66.67
				<i>csb_clk</i> Freq	uency (MHz)	
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			
High	0010	4 : 1		100	133	266
High	0011	6 : 1	100	150	200	
High	0100	8 : 1	133	200	266	
High	0101	10 : 1	166	250	333	
High	0110	12 : 1	200	300		
High	0111	14 : 1	233			
High	1000	16 : 1	266			

Table 60. CSB Frequency Options for Agent Mode (continued)

¹ CFG_CLKIN_DIV doubles csb_clk if set high.

² CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

19.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 61 shows the encodings for RCWL[COREPLL]. COREPLL values that are not listed in Table 61 should be considered as reserved.

NOTE

Core VCO frequency = core frequency × VCO divider

VCO divider must be set properly so that the core VCO frequency is in the range of 800–1800 MHz.

19.3 Suggested PLL Configurations

Table 62 shows suggested PLL configurations for 33 and 66 MHz input clocks.

Table 62. Sug	gested PLL	Configurations
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	RC	RCWL 400 MHz Device		0 MHz Dev	ice	533	3 MHz Dev	ice	667	667 MHz Device		
Ref No. ¹	SPMF	CORE PLL	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)	Input Clock Freq (MHz) ²	CSB Freq (MHz)	Core Freq (MHz)	
				33 N	MHz CLKIN	/PCI_CLK	Options					
922	1001	0100010	—	—	—	_	—	f300	33	300	300	
723	0111	0100011	33	233	350	33	233	350	33	233	350	
604	0110	0000100	33	200	400	33	200	400	33	200	400	
624	0110	0100100	33	200	400	33	200	400	33	200	400	
803	1000	0000011	33	266	400	33	266	400	33	266	400	
823	1000	0100011	33	266	400	33	266	400	33	266	400	
903	1001	0000011		_		33	300	450	33	300	450	
923	1001	0100011	—		33	300	450	33	300	450		
704	0111	0000011	—			33	233	466	33	233	466	
724	0111	0100011		_			233	466	33	233	466	
A03	1010	0000011		_		33	333	500	33	333	500	
804	1000	0000100		_		33	266	533	33	266	533	
705	0111	0000101		_			_		33	233	583	
606	0110	0000110		_			—		33	200	600	
904	1001	0000100		_			_		33	300	600	
805	1000	0000101		_			_		33	266	667	
A04	1010	0000100		_			_		33	333	667	
				66 N	MHz CLKIN	/PCI_CLK	Options					
304	0011	0000100	66	200	400	66	200	400	66	200	400	
324	0011	0100100	66	200	400	66	200	400	66	200	400	
403	0100	0000011	66	266	400	66	266	400	66	266	400	
423	0100	0100011	66	266	400	66	266	400	66	266	400	
305	0011	0000101				66	200	500	66	200	500	
503	0101	0000011		_		66	333	500	66	333	500	
404	0100	0000100		_		66	266	533	66	266	533	

Table 63. Package Thermal Characteristics for TBGA (continued)

Characteristic	Symbol	Value	Unit	Notes
Junction-to-package natural convection on top	ΨJT	1	°C/W	6

Notes:

- 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
- 3. Per JEDEC JESD51-6 with the board horizontal, 1 m/s is approximately equal to 200 linear feet per minute (LFM).
- 4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- 6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

20.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See Table 5 for I/O power dissipation values.

20.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

 T_J = junction temperature (°C)

 T_A = ambient temperature for the package (°C)

 $R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

 P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter

Thermal

(edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

 $T_J = T_A + (R_{\theta JA} \times P_D)$

where:

 T_J = junction temperature (°C)

 T_A = ambient temperature for the package (°C)

 $R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

 P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

20.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

 T_J = junction temperature (°C)

 T_T = thermocouple temperature on top of package (°C)

 Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)

 P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

Rev. Number	Date	Substantive Change(s)
9	2/2009	 Added footnote 6 to Table 7. In Section 9.2, "USB AC Electrical Specifications," clarified that AC table is for ULPI only. In Table 39, corrected t_{LBKHOV} parameter to t_{LBKLOV} (output data is driven on falling edge of clock in DLL bypass mode). Similarly, made the same correction to Figure 22, Figure 24, and Figure 25 for output signals. Added footnote 11 to Table 55. Added footnote 4 to Table 66. In Section 21.1, "System Clocking," removed "(AVDD1)" and "(AVDD2") from bulleted list. In Section 21.2, "PLL Power Supply Filtering," in the second paragraph, changed "provide five independent filter circuits," and "the five AVDD pins" to provide four independent filter circuits," and "the four AVDD pins." In Table 57, corrected the max csb_clk to 266 MHz. In Table 62, added PLL configurations 903, 923, A03, A23, and 503 for 533 MHz In Table 66, updated note 1 to say the following: "For temperature range = C, processor frequency is limited to 533 with a platform frequency of 266."
8	4/2007	 In Table 3, "Output Drive Capability," changed the values in the Output Impedance column and added USB to the seventh row. In Section 21.7, "Pull-Up Resistor Requirements, "deleted last two paragraphs and after first paragraph, added a new paragraph. Deleted Section 21.8, "JTAG Configuration Signals," and Figure 43, "JTAG Interface Connection."
7	3/2007	 In Table 57, "Operating Frequencies for TBGA," in the 'Coherent system bus frequency (<i>csb_clk</i>)' row, changed the value in the 533 MHz column to 100-333. In Table 63, "Suggested PLL Configurations," under the subhead, '33 MHz CLKIN/PCI_CLK Options,' added row A03 between Ref. No. 724 and 804. Under the subhead '66 MHz CLKIN/PCI_CLK Options,' added row 503 between Ref. No. 305 and 404. For Ref. No. 306, changed the CORE PLL value to 0000110. In Section 23, "Ordering Information," replaced first paragraph and added a note. In Section 23.1, "Part Numbers Fully Addressed by this Document," replaced first paragraph.
6	2/2007	 Page 1, updated first paragraph to reflect PowerQUICC II Pro information. In Table 18, "DDR and DDR2 SDRAM Input AC Timing Specifications," added note 2 to t_{CISKEW} and deleted original note 3; renumbered the remaining notes. In Figure 41, "JTAG Interface Connection," updated with new figure. In Section 23.1, "Part Numbers Fully Addressed by This Document," replaced third sentence of first paragraph directing customer to product summary page for available frequency configuration parts.
5	1/2007	 In Table 1, "Absolute Maximum Ratings," added (1.36 max for 667-MHz core frequency) to max V_{DD} and Av_{DD} values. In Table 2, "Recommended Operating Conditions," added a row showing nominal core supply voltage and PLL supply voltage of 1.3 V for 667-MHz parts. In Table 4, "MPC8349EA Power Dissipation," added two footnotes to 667-MHz row showing nominal core supply voltage and PLL supply voltage of 1.3 V for 667-MHz parts. In Table 54, "MPC83479EA (TBGA) Pinout Listing," updated V_{DD} nd AV_{DD} rows to show nominal core supply voltage and PLL supply voltage of 1.3 V for 667-MHz parts.
4	12/2006	Table 19, "DDR and DDR2 SDRAM Output AC Timing Specifications," modified T _{ddkhds} for 333 MHz from 900 ps to 775 ps.